MICROWAVE POWER GaAs FET
TIM5964-60SL-422

FEATURES

- **BROAD BAND INTERNALLY MATCHED FET**
- **HIGH POWER**
  P1dB= 48.0dBm at 5.85GHz to 6.75GHz
- **HIGH GAIN**
  G1dB= 8.0dB at 5.85GHz to 6.75GHz
- **LOW INTERMODULATION DISTORTION**
  IM3= -45dBc at Pout= 36.5dBm (Single Carrier Level)
- **HERMETICALLY SEALED PACKAGE**

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 9.5A f= 5.85 to 6.75GHz	dBm	47.0	48.0	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	7.0	8.0	—
Drain Current	IDS1		A	—	13.2	15.0
Gain Flatness	ΔG		dB	—	—	±0.8
Power Added Efficiency	ηadd		%	—	40	—
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 36.5dBm, Δf= 5MHz (Single Carrier Level)	dBc	-40	-45	—
Drain Current	IDS2		A	—	—	11.8
Channel Temperature Rise	ΔTch	(VDS × IDS + Pin − P1dB) × Rth(c-c)	°C	—	—	100

Recommended Gate Resistance(Rg): 28 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 12.0A	S	—	20	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 200mA	V	-1.0	-1.8	-3.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	38	—
Gate-Source Breakdown Voltage	VGSO	IGS= -1.0mA	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	0.6	0.8

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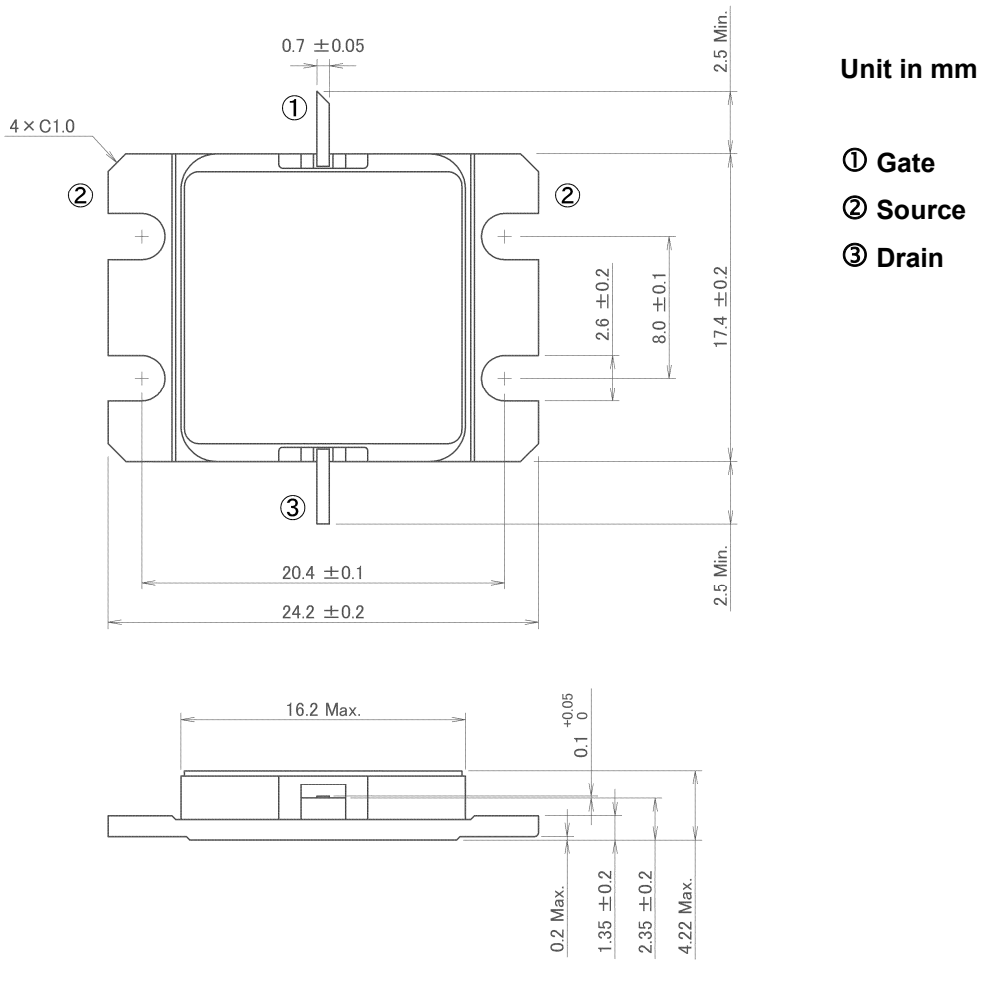
ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	20
Total Power Dissipation (Tc= 25°C)	PT	W	187.5
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-16G1B)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

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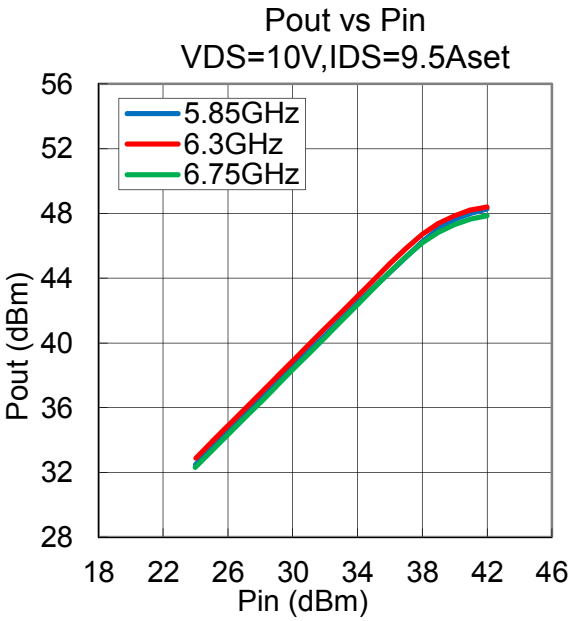
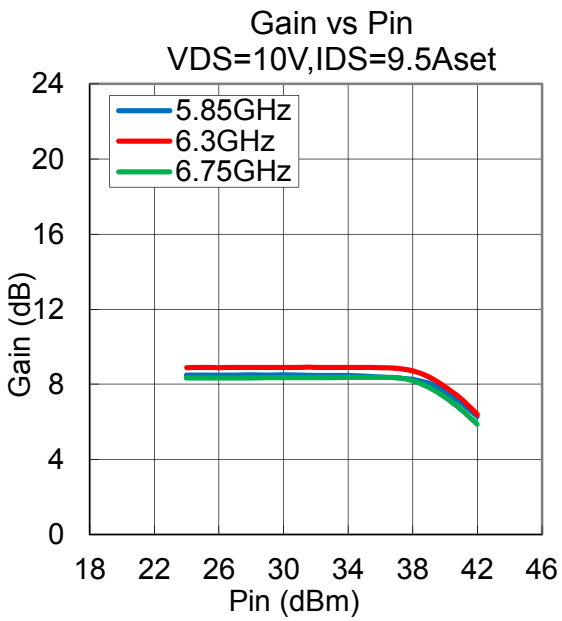
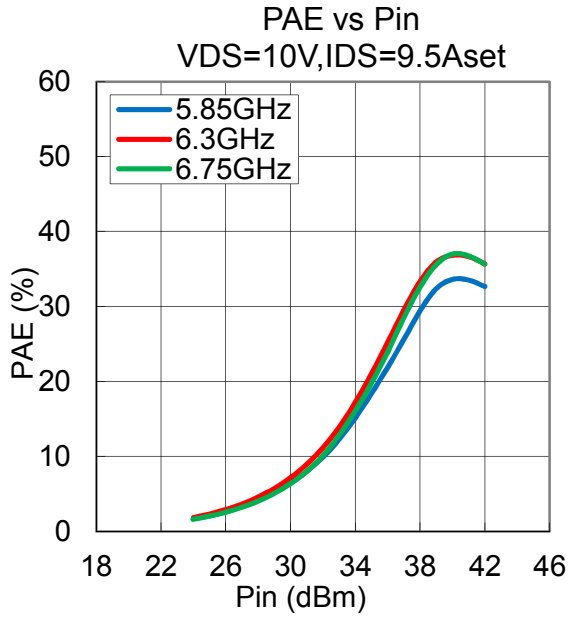
TYPICAL RF PERFORMANCE

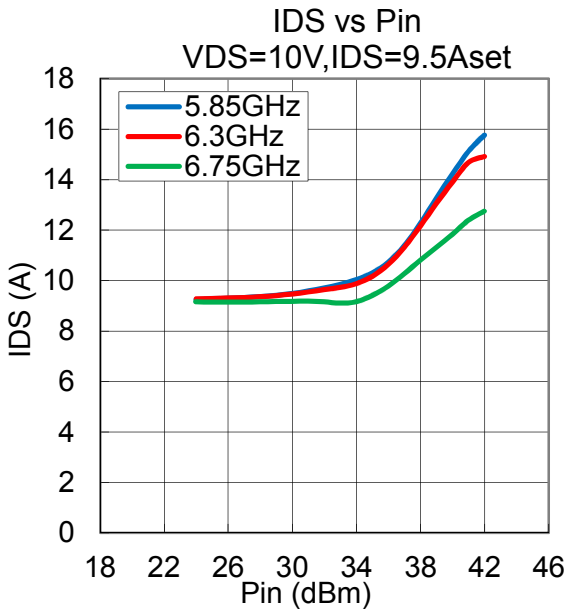
·Pout , Gain , PAE , IDS vs. Pin

VDS= 10 V, IDSset= 9.5 A, f= 5.85, 6.3, 6.75 GHz, Ta= +25 ℃









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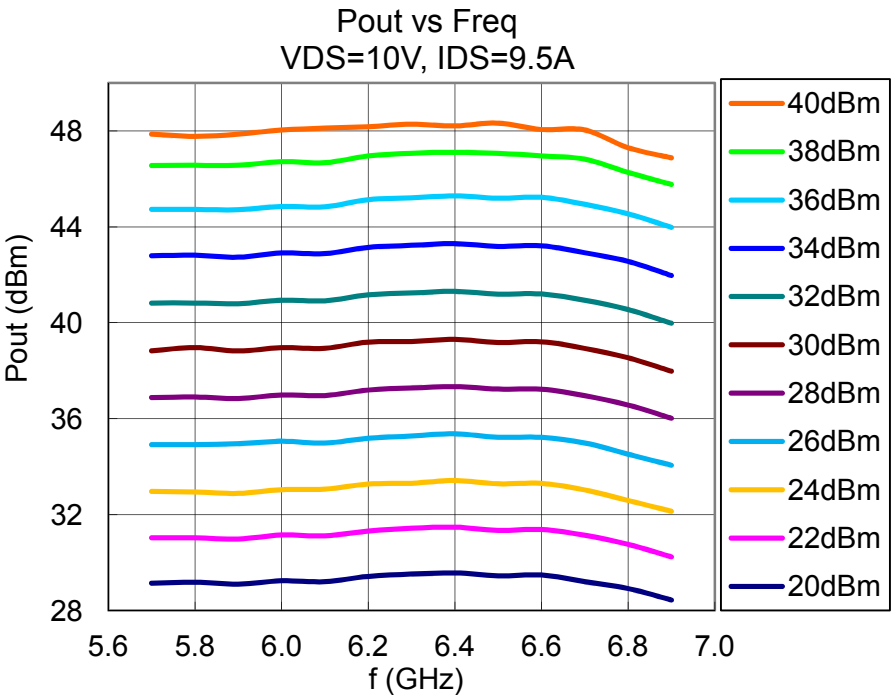
·Pout vs. Frequency

VDS= 10 V, IDSset= 9.5 A, Ta= +25 °C



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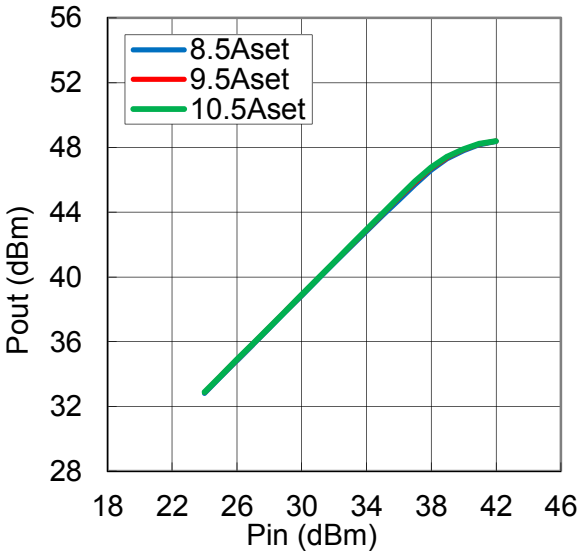
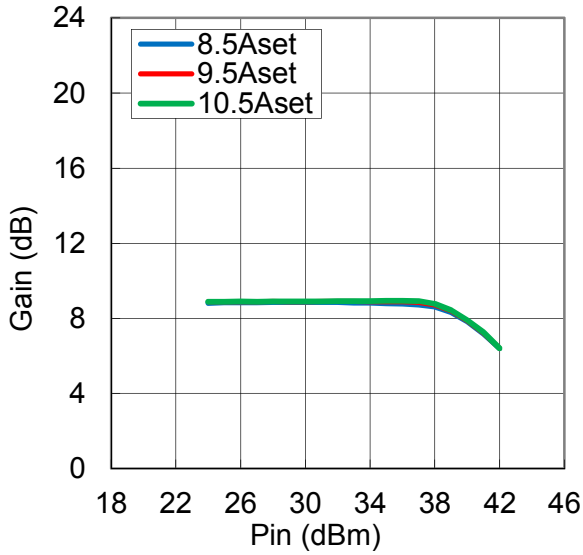
·Pout , Gain , PAE , IDS vs. Pin vs. IDSset

VDS= 10V, IDSset= 8.5, 9.5, 10.5 A, f= 6.3 GHz, Ta= +25 ℃

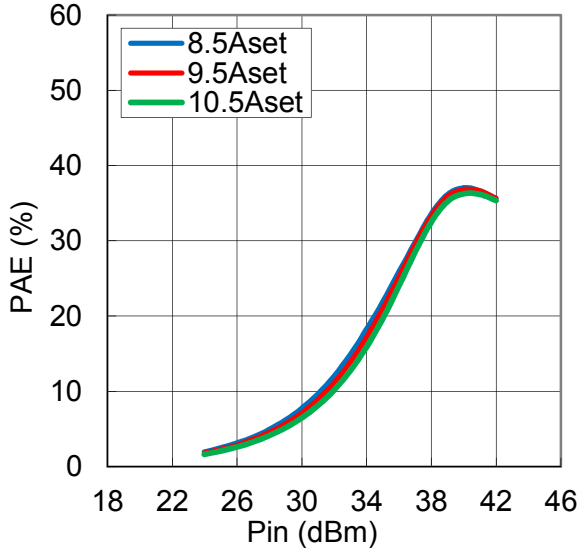
Pout vs Pin
VDS=10V,f=6.3GHz



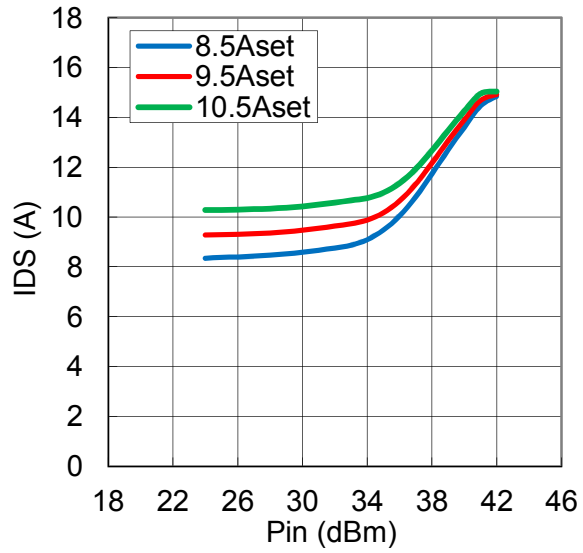
Gain vs Pin
VDS=10V,f=6.3GHz



PAE vs Pin
VDS=10V,f=6.3GHz



IDS vs Pin
VDS=10V,f=6.3GHz



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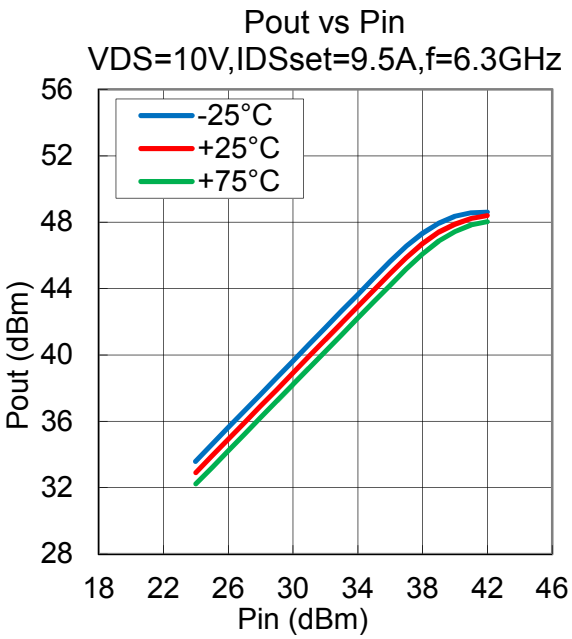
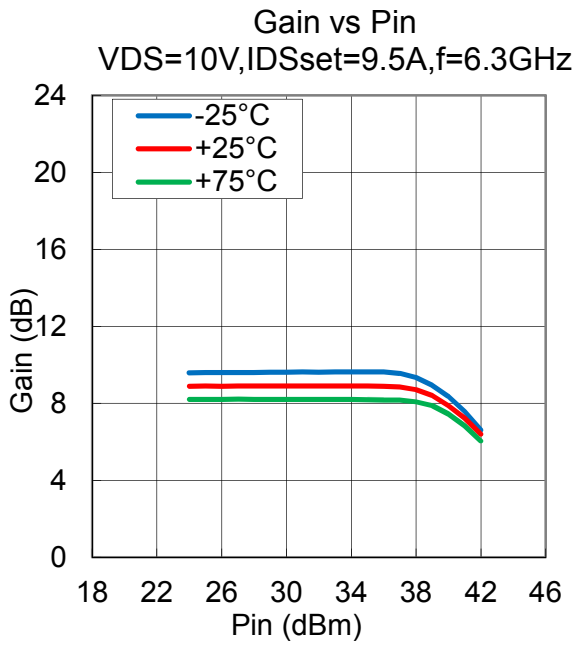
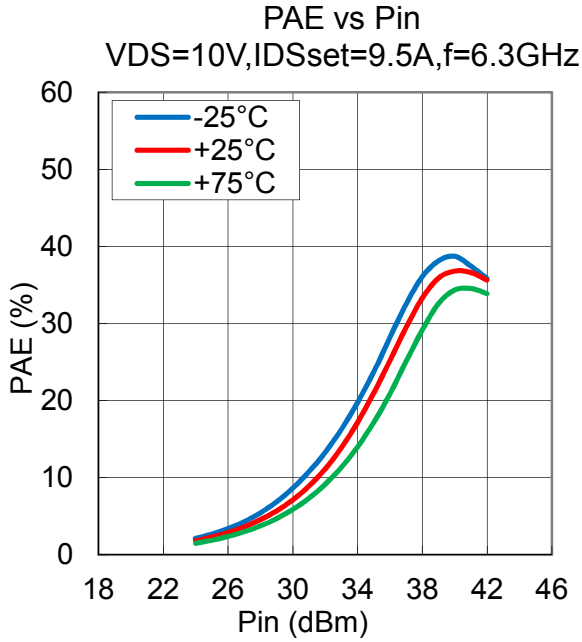
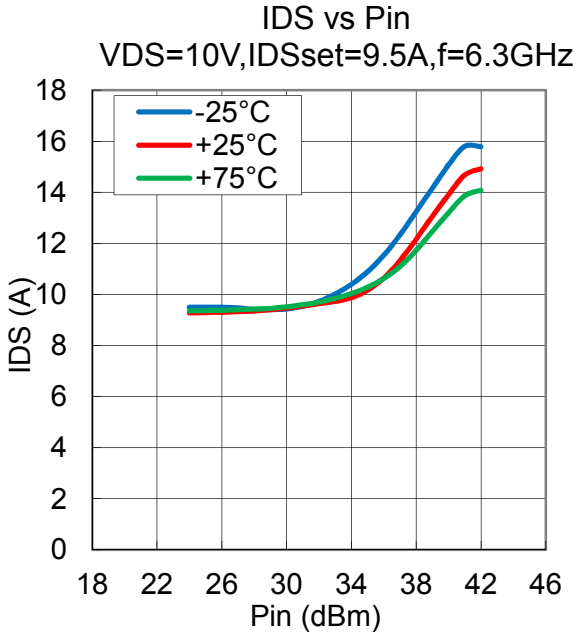
·Pout , Gain , PAE , IDS vs. Pin vs. Temperature

VDS= 10 V, IDSset= 9.5 A, f= 6.3 GHz, Ta= -25, +25, +75 ℃









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